

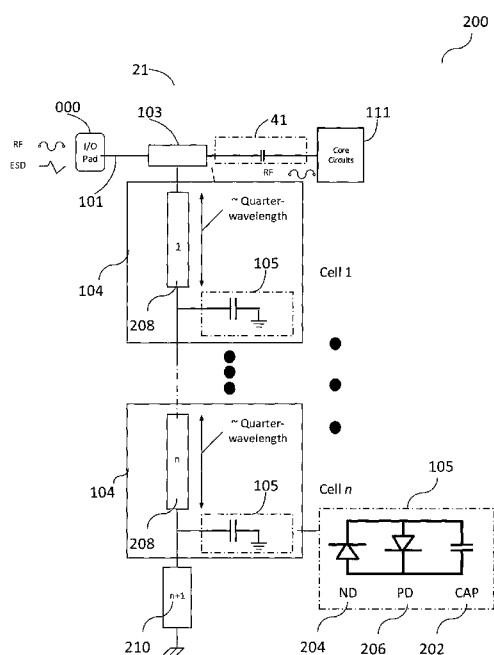


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(54) Title: MINIATURE PASSIVE STRUCTURES, HIGH FREQUENCY ELECTROSTATIC DISCHARGE PROTECTION NETWORKS, AND HIGH FREQUENCY ELECTROSTATIC DISCHARGE PROTECTION SCHEMES



(57) Abstract: According to various embodiments, a miniature passive structure for electrostatic discharge protection and input/output matching for a high frequency integrated circuit may be provided. The structure may include: either a transmission line or an inductor for providing at least one electrostatic discharge path; and a capacitor with a first end connected to the transmission line or inductor and a second end connected to ground.